

MITSUBISHI IGBT MODULES
CM100TU-12F

HIGH POWER SWITCHING USE

CM100TU-12F



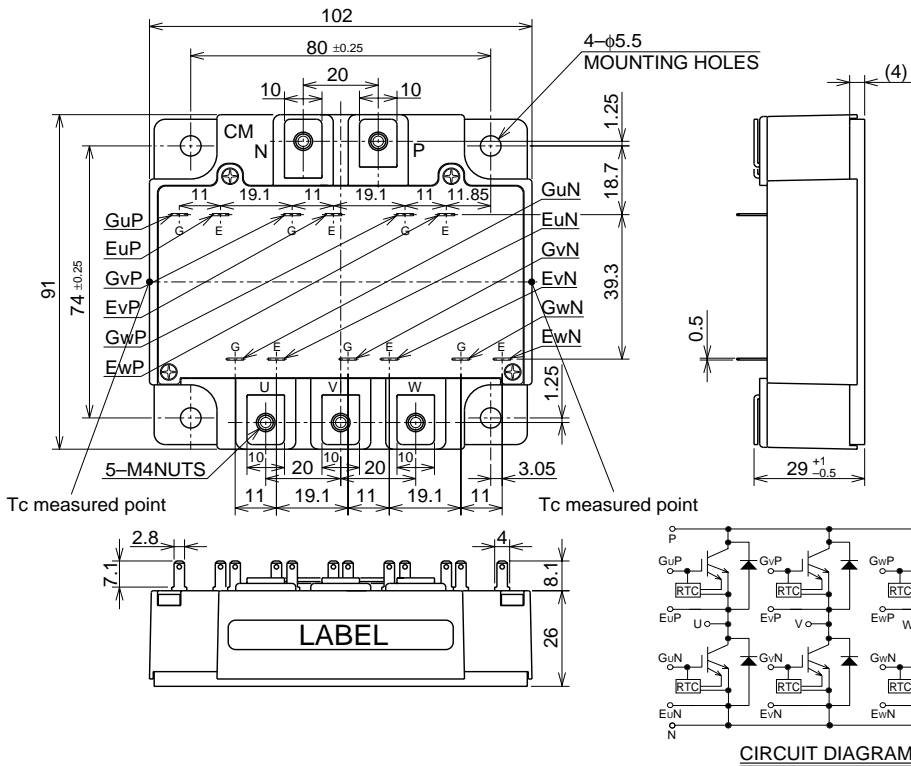
- Ic 100A
- VCES 600V
- Insulated Type
- 6-elements in a pack

APPLICATION

General purpose inverters & Servo controls, etc

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Aug. 1999



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MAXIMUM RATINGS (T_j = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	600	V
V _{GES}	Gate-emitter voltage	C-E Short	±20	V
I _C	Collector current	T _C = 25°C	100	A
I _{CM}		Pulse (Note 2)	200	
I _E (Note 1)	Emitter current	T _C = 25°C	100	A
I _{EM} (Note 1)		Pulse (Note 2)	200	
P _C (Note 3)	Maximum collector dissipation	T _C = 25°C	350	W
T _j	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +125	°C
V _{iso}	Isolation voltage	Main terminal to base plate, AC 1 min.	2500	V
—	Torque strength	Main Terminal M4	1.3 ~ 1.7	N • m
—		Mounting holes M5	2.5 ~ 3.5	N • m
—	Weight	Typical value	570	g

ELECTRICAL CHARACTERISTICS (T_j = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{CES}	Collector cutoff current	V _{CE} = V _{CES} , V _{GE} = 0V	—	—	1	mA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C = 10mA, V _{CE} = 10V	5	6	7	V	
I _{GES}	Gate leakage current	V _{GE} = V _{CES} , V _{CE} = 0V	—	—	20	μA	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C = 100A, V _{GE} = 15V	T _j = 25°C	1.6	2.2	V	
			T _j = 125°C	1.6	—		
C _{ies}	Input capacitance	V _{CE} = 10V V _{GE} = 0V	—	—	27	nF	
C _{oes}	Output capacitance		—	—	1.8		
C _{res}	Reverse transfer capacitance		—	—	1		
Q _G	Total gate charge	V _{CC} = 300V, I _C = 100A, V _{GE} = 15V	—	620	—	nC	
t _{d(on)}	Turn-on delay time	V _{CC} = 300V, I _C = 100A V _{GE1} = V _{GE2} = 15V R _G = 6.3Ω, Inductive load switching operation I _E = 100A	—	—	100	ns	
t _r	Turn-on rise time		—	—	80		
t _{d(off)}	Turn-off delay time		—	—	300		
t _f	Turn-off fall time		—	—	250		
t _{rr} (Note 1)	Reverse recovery time		—	—	150		
Q _{rr} (Note 1)	Reverse recovery charge		—	1.9	—		μC
V _{EC} (Note 1)	Emitter-collector voltage		I _E = 100A, V _{GE} = 0V	—	—		2.6
R _{th(j-c)Q}	Thermal resistance ^{*1}	IGBT part (1/6 module)	—	—	0.35	°C/W	
R _{th(j-c)R}		FWDi part (1/6 module)	—	—	0.70		
R _{th(c-f)}	Contact thermal resistance	Case to fin, Thermal compound applied ^{*2} (1/6 module)	—	0.11	—		
R _{th(j-c)Q}	Thermal resistance	T _c measured point is just under the chips	—	—	0.28 ^{*3}		
R _G	External gate resistance		6.3	—	63	Ω	

Note 1. I_E, V_{EC}, t_{rr}, Q_{rr}, die/dt represent characteristics of the anti-parallel, emitter to collector free-wheel diode. (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (T_j) does not exceed T_{jmax} rating.

3. Junction temperature (T_j) should not increase beyond 150°C.

4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

*1 : T_c measured point is indicated in OUTLINE DRAWING.

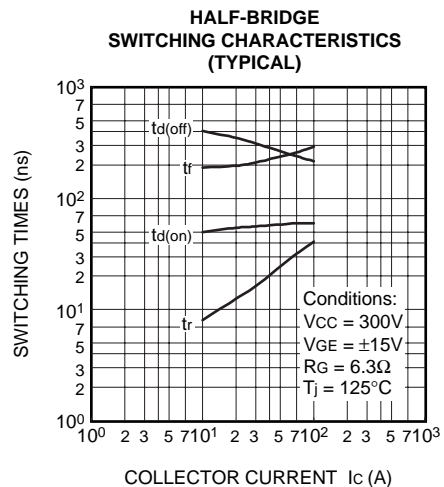
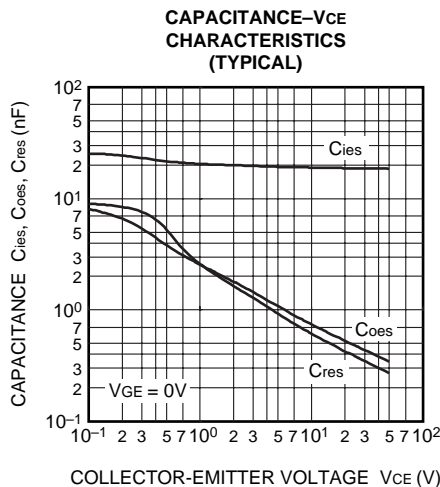
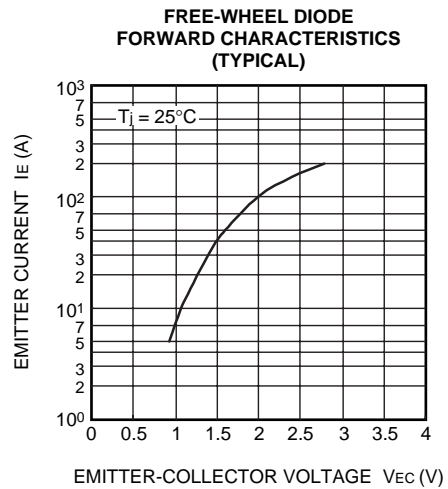
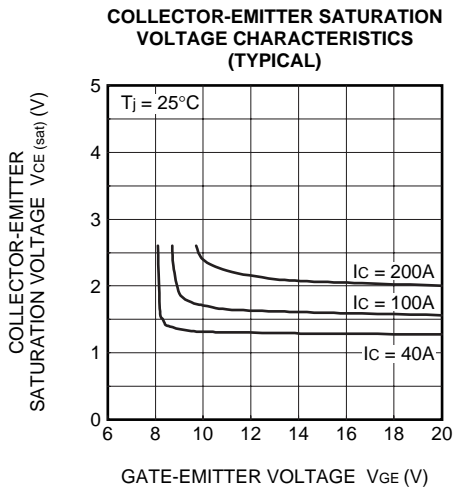
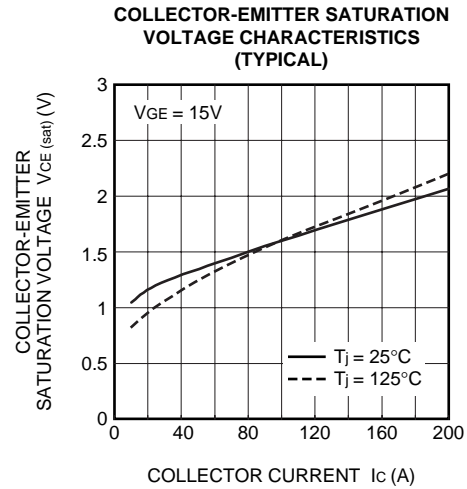
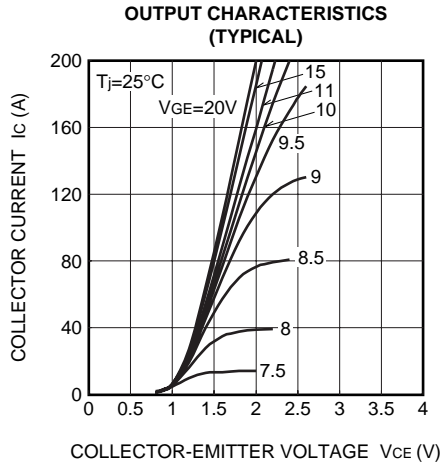
*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

*3 : If you use this value, R_{th(f-a)} should be measured just under the chips.

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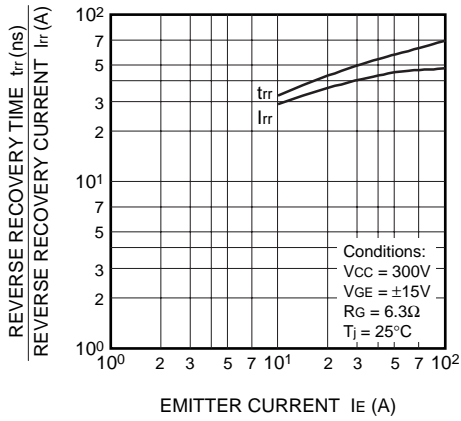
PERFORMANCE CURVES



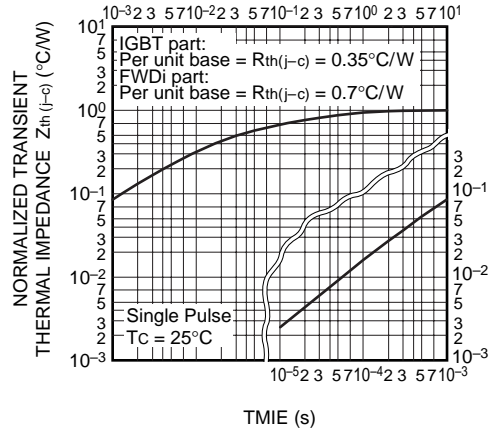
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HIGH POWER SWITCHING USE

REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part & FWDi part)



GATE CHARGE CHARACTERISTICS (TYPICAL)

